

HiPerFET™

Power MOSFETs

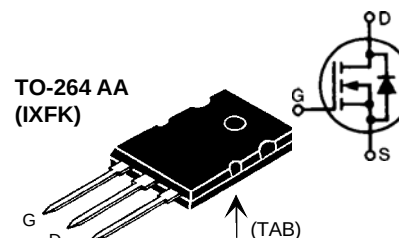
IXFK / IXFN 44 N50
IXFK / IXFN 48 N50

N-Channel Enhancement Mode
Avalanche Rated, High dv/dt, Low t_{rr}

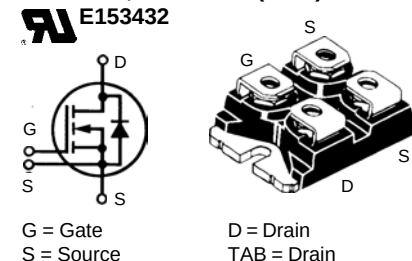
V_{DSS}	I_{D25}	$R_{DS(on)}$
500 V	44 A	0.12 Ω
500 V	48 A	0.10 Ω
$t_{rr} \leq 250$ ns		

Symbol	Test Conditions	Maximum Ratings		
		IXFK	IXFN	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	500	500	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1$ M Ω	500	500	V
V_{GS}	Continuous	± 20	± 20	V
V_{GSM}	Transient	± 30	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	44N50	44	A
		48N50	48	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	44N50	176	A
		48N50	192	A
I_{AR}	$T_C = 25^\circ\text{C}$	24	24	A
E_{AR}	$T_C = 25^\circ\text{C}$	30	30	mJ
dv/dt	$I_S \leq I_{DM}$, di/dt ≤ 100 A/ μs , $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2$ Ω	5	5	V/ns
P_D	$T_C = 25^\circ\text{C}$	500	520	W
T_J		-55 ... +150		$^\circ\text{C}$
T_{JM}		150		$^\circ\text{C}$
T_{stg}		-55 ... +150		$^\circ\text{C}$
T_L	1.6 mm (0.063 in) from case for 10 s	300	-	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS $t = 1$ min	-	2500	V~
	$I_{ISOL} \leq 1$ mA $t = 1$ s	-	3000	V~
M_d	Mounting torque	0.9/6	1.5/13	Nm/lb.in.
	Terminal connection torque	-	1.5/13	Nm/lb.in.
Weight		10	30	g

Symbol	Test Conditions	Characteristic Values (T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
V _{DSS}	V _{GS} = 0 V, I _D = 1 mA	500		V
V _{GS(th)}	V _{DS} = V _{GS} , I _D = 8 mA	2		V
I _{GSS}	V _{GS} = ±20 V _{DC} , V _{DS} = 0			±200 nA
I _{DSS}	V _{DS} = 0.8 • V _{DSS}	T _J = 25°C		400 μA
	V _{GS} = 0 V	T _J = 125°C		2 mA
R _{DS(on)}	V _{GS} = 10 V, I _D = 0.5 • I _{D25}	44N50		0.12 Ω
		48N50		0.10 Ω
	Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			



miniBLOC, SOT-227 B (IXFN)



Either Source terminal at miniBLOC can be used as Main or Kelvin Source

Features

- International standard packages
- Molding epoxies meet UL 94 V-0 flammability classification
- SOT-227B miniBLOC with aluminium nitride isolation
- Low $R_{DS(on)}$ HDMOS™ process
- Unclamped Inductive Switching (UIS) rated
- Fast intrinsic rectifier

Applications

- DC-DC converters
- Synchronous rectification
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- Temperature and lighting controls

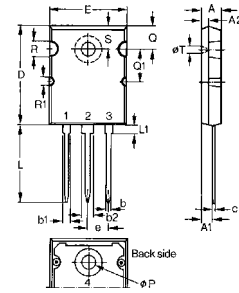
Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$, pulse test	22	42	S
C_{iss} C_{oss} C_{rss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		8400 900 280	pF pF pF
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1\ \Omega$ (External),		30 60 100 30	ns ns ns ns
$Q_{g(on)}$ Q_{gs} Q_{gd}	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		270 60 135	nC nC nC
R_{thJC} R_{thCK}	TO-264 AA TO-264 AA		0.15	0.25 K/W K/W
R_{thJC} R_{thCK}	miniBLOC, SOT-227 B miniBLOC, SOT-227 B		0.05	0.24 K/W K/W

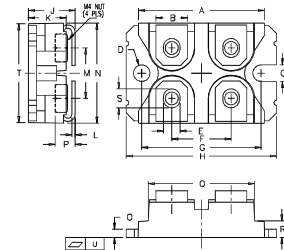
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$			48 A
I_{SM}	Repetitive; pulse width limited by T_{JM}			192 A
V_{SD}	$I_F = 100\text{ A}, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5 V
t_{rr} Q_{RM} I_{RM}	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$		TBD 20	250 ns μC A

TO-264 AA Outline



Dim.	Millimeter Min. Max.	Inches Min. Max.
A	4.82 5.13	.190 .202
A1	2.54 2.89	.100 .114
A2	2.00 2.10	.079 .083
b	1.12 1.42	.044 .056
b1	2.39 2.69	.094 .106
b2	2.90 3.09	.114 .122
c	0.53 0.83	.021 .033
D	25.91 26.16	1.020 1.030
E	19.81 19.96	.780 .786
e	5.46 BSC	.215 BSC
J	0.00 0.25	.000 .010
K	0.00 0.25	.000 .010
L	20.32 20.83	.800 .820
L1	2.29 2.59	.090 .102
P	3.17 3.66	.125 .144
Q	6.07 6.27	.239 .247
Q1	8.38 8.69	.330 .342
R	3.81 4.32	.150 .170
R1	1.78 2.29	.070 .090
S	6.04 6.30	.238 .248
T	1.57 1.83	.062 .072

miniBLOC, SOT-227 B



M4 screws (4x) supplied

Dim.	Millimeter Min. Max.	Inches Min. Max.
A	31.50 31.88	1.240 1.255
B	7.80 8.20	0.307 0.323
C	4.09 4.29	0.161 0.169
D	4.09 4.29	0.161 0.169
E	4.09 4.29	0.161 0.169
F	14.91 15.11	0.587 0.595
G	30.12 30.30	1.186 1.193
H	38.00 38.23	1.496 1.505
J	11.68 12.22	0.460 0.481
K	8.92 9.60	0.351 0.378
L	0.76 0.84	0.030 0.033
M	12.60 12.85	0.496 0.506
N	25.15 25.42	0.990 1.001
O	1.98 2.13	0.078 0.084
P	4.95 5.97	0.195 0.235
Q	26.54 26.90	1.045 1.059
R	3.94 4.42	0.155 0.174
S	4.72 4.85	0.186 0.191
T	24.59 25.07	0.968 0.987
U	-0.05 0.1	-0.002 0.004

Fig. 1 Output Characteristics

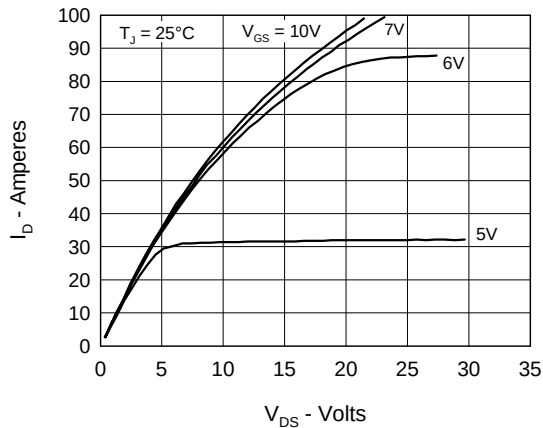


Fig. 2 Input Admittance

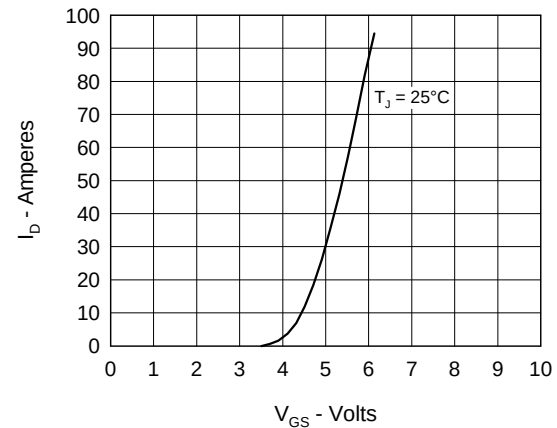


Fig. 3 $R_{DS(on)}$ vs. Drain Current

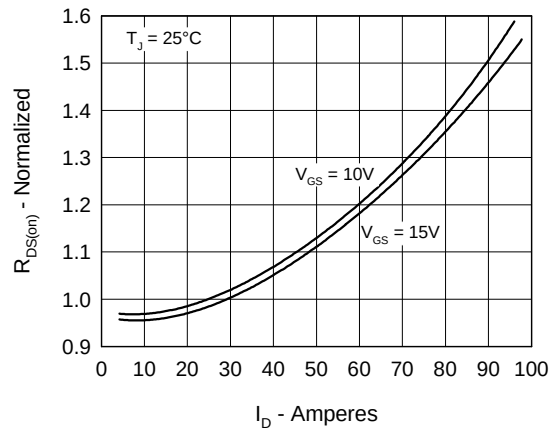


Fig. 4 Temperature Dependence of Drain to Source Resistance

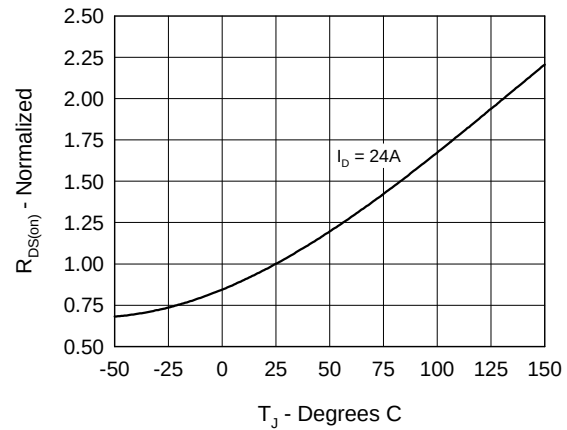


Fig. 5 Drain Current vs. Case Temperature

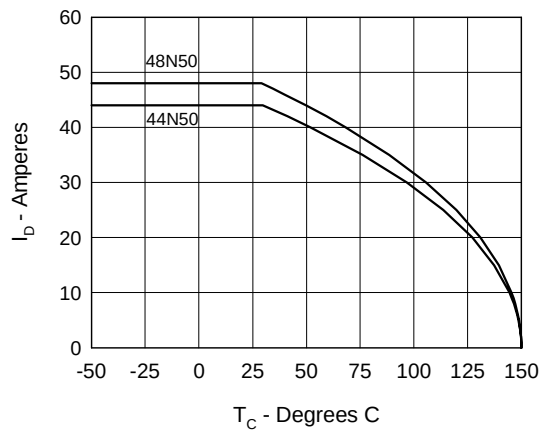


Fig. 6 Temperature Dependence of Breakdown and Threshold Voltage

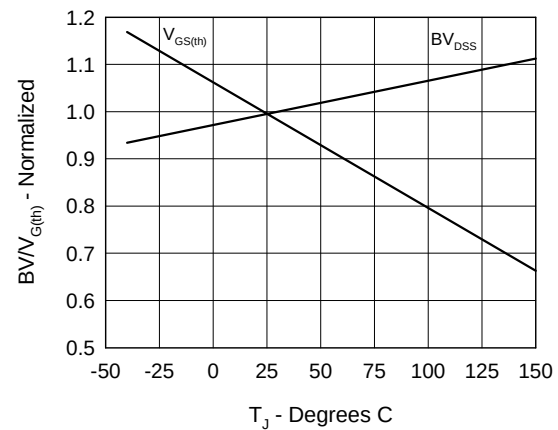


Fig.7 Gate Charge Characteristic Curve

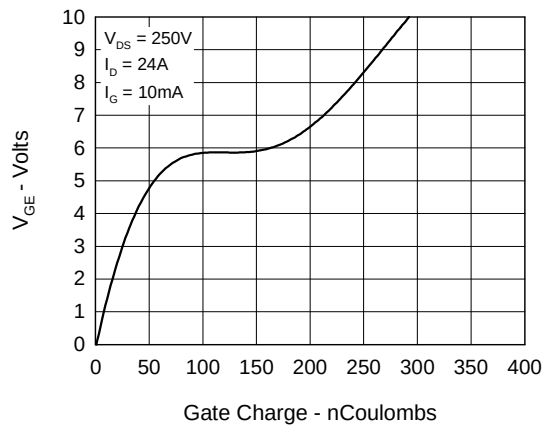


Fig.8 Capacitance Curves

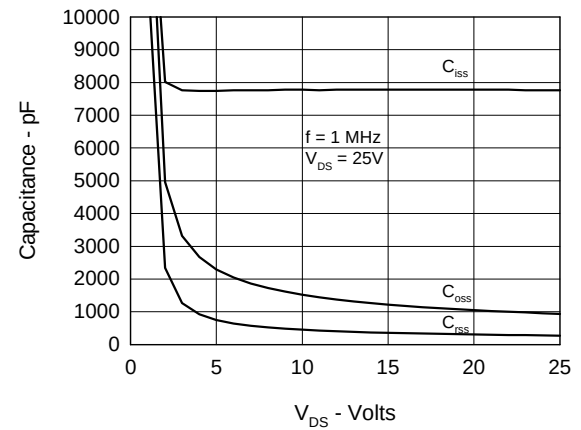


Fig.9 Source Current vs. Source to Drain Voltage

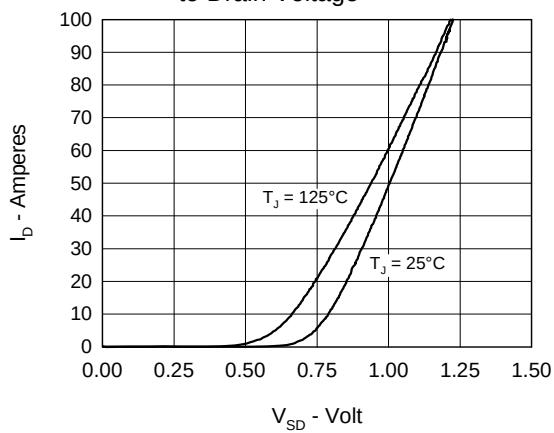


Fig.10 Transient Thermal Impedance

